

What is claimed is:

- 1 1. A semiconductor integrated circuit comprising a power supply
2 wiring and a ground wiring and a decoupling capacitor formed
3 between said power supply wiring and said ground wiring,
4 wherein at least one of the electrodes of said decoupling
5 capacitor consists of a shield layer formed in a plane shape
6 on a semiconductor substrate, and said shield layer is
7 connected electrically directly to the semiconductor
8 substrate and is fixed to a power supply potential or the
9 ground potential.
- 1 2. The semiconductor integrated circuit as claimed in claim
2 1, wherein, out of the electrodes of said decoupling capacitor,
3 the electrode opposing the electrode consisting of said shield
4 layer consists of a wiring layer connected to wirings on the
5 uppermost layer of a multilayer wiring structure via contact
6 electrodes, and a capacitor insulating film for forming said
7 decoupling capacitor is provided between said wiring layer
8 and said shield layer.
- 1 3. A semiconductor integrated circuit comprising a power supply
2 wiring and a ground wiring and a decoupling circuit formed
3 between said power supply wiring and said ground wiring,
4 wherein at least one electrode of said decoupling capacitor
5 consists of a shield layer obtained by covering a plurality
6 of protrusions formed on a semiconductor substrate, and said
7 shield layer is electrically connected directly to the
8 semiconductor substrate and is fixed to a power supply

9 potential or the ground potential.

1 4. The semiconductor integrated circuit as claimed in claim 3,
2 wherein said protrusions are formed simultaneously with a
3 gate electrode by the identical formation process for the
4 gate electrode.

1 5. The semiconductor integrated circuit as claimed in claim 1
2 or 3, wherein said decoupling capacitor is formed on an element
3 isolation oxide film.

1 6. The semiconductor integrated circuit as claimed in claim 1
2 or 3, wherein said shield layer consists of a silicon compound
3 of a metal.